

MOSFET – N-Channel, SUPERFET[®] II, Easy-Drive

600 V, 29 A, 125 mΩ

FCH125N60E

Description

SUPERFET II MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SUPERFET II MOSFET easy-drive series offers slightly slower rise and fall times compared to the SUPERFET II MOSFET series. Noted by the "E" part number suffix, this family helps manage EMI issues and allows for easier design implementation. For faster switching in applications where switching losses must be at an absolute minimum, please consider the SUPERFET II MOSFET series.

Features

- Typ. $R_{DS(on)} = 102 \text{ m}\Omega$
- 650 V @ $T_J = 150^\circ\text{C}$
- Ultra Low Gate Charge (Typ. $Q_g = 75 \text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 258 \text{ pF}$)
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Telecom / Server Power Supplies
- Industrial Power Supplies



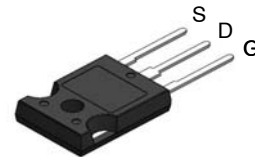
ON Semiconductor[®]

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| V_{DS} | $R_{DS(on)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|----------|--------------------------|-------------------|
| 600 V | 125 mΩ @ 10 V | 29 A |

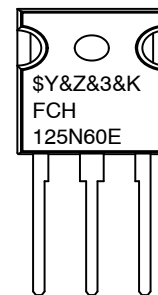


N-CHANNEL MOSFET



TO-247-3LD
CASE 340CK

MARKING DIAGRAM



- \$Y = ON Semiconductor Logo
- &Z = Assembly Plant Code
- &3 = Numeric Date Code
- &K = Lot Code
- FCH125N60E = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FCH125N60E

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

| Symbol | Parameter | FCH125N60E | Unit |
|-----------------------------------|--|---------------------------------------|------|
| V _{DSS} | Drain to Source Voltage | 600 | V |
| V _{GSS} | Gate to Source Voltage | - DC | ±20 |
| | | - AC (f > 1 Hz) | ±30 |
| I _D | Drain Current: | - Continuous (T _C = 25°C) | 29 |
| | | - Continuous (T _C = 100°C) | 18 |
| I _{DM} | Drain Current: | - Pulsed (Note 1) | 87 |
| E _{AS} | Single Pulsed Avalanche Energy (Note 2) | 720 | mJ |
| I _{AR} | Avalanche Current (Note 1) | 6 | A |
| E _{AR} | Repetitive Avalanche Energy (Note 1) | 2.78 | mJ |
| dv/dt | MOSFET dv/dt | 100 | V/ns |
| | Peak Diode Recovery dv/dt (Note 3) | 20 | |
| P _D | Power Dissipation | (T _C = 25°C) | 278 |
| | | - Derate Above 25°C | 2.2 |
| T _J , T _{STG} | Operating and Storage Temperature Range | -55 to + 150 | °C |
| T _L | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | 300 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I_{AS} = 6.0 A, R_G = 25 Ω, Starting T_J = 25 °C.
3. I_{SD} ≤ 14.5 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 380 V, Starting T_J = 25 °C.

PACKAGE MARKING AND ORDERING INFORMATION

| Part Number | Top Marking | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|-------------|---------|----------------|-----------|------------|----------|
| FCH125N60E | FCH125N60E | TO-247 | Tube | N/A | N/A | 30 Units |

THERMAL CHARACTERISTICS

| Symbol | Parameter | FCH125N60E | Unit |
|------------------|---|------------|------|
| R _{θJC} | Thermal Resistance, Junction to Case, Max. | 0.45 | °C/W |
| R _{θJA} | Thermal Resistance, Junction to Ambient, Max. | 40 | |

FCH125N60E

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Unit |
|--------|-----------|----------------|------|------|------|------|
|--------|-----------|----------------|------|------|------|------|

OFF CHARACTERISTICS

| | | | | | | |
|--------------------------------------|---|---|-----|-----|------|------|
| BV _{DSS} | Drain to Source Breakdown Voltage | I _D = 10 mA, V _{GS} = 0 V, T _J = 25°C | 600 | – | – | V |
| | | I _D = 10 mA, V _{GS} = 0 V, T _J = 150°C | 650 | – | – | |
| ΔBV _{DSS} / ΔT _J | Breakdown Voltage Temperature Coefficient | I _D = 10 mA, Referenced to 25°C | – | 0.7 | – | V/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 600 V, V _{GS} = 0 V | – | – | 1 | μA |
| | | V _{DS} = 480 V, V _{GS} = 0 V, T _C = 125 °C | – | 2 | – | |
| I _{GSS} | Gate to Body Leakage Current | V _{GS} = ±20 V, V _{DS} = 0 V | – | – | ±100 | nA |

ON CHARACTERISTICS

| | | | | | | |
|---------------------|--------------------------------------|---|-----|-----|-----|----|
| V _{GS(th)} | Gate Threshold Voltage | V _{GS} = V _{DS} , I _D = 250 μA | 2.5 | – | 3.5 | V |
| R _{DS(on)} | Static Drain to Source On Resistance | V _{GS} = 10 V, I _D = 14.5 A | – | 102 | 125 | mΩ |
| g _{FS} | Forward Transconductance | V _{DS} = 20 V, I _D = 14.5 A | – | 25 | – | S |

DYNAMIC CHARACTERISTICS

| | | | | | | |
|------------------------|-------------------------------|---|---|------|------|----|
| C _{iss} | Input Capacitance | V _{DS} = 380 V, V _{GS} = 0 V, f = 1 MHz | – | 2250 | 2990 | pF |
| C _{oss} | Output Capacitance | | – | 60 | 80 | pF |
| C _{rss} | Reverse Transfer Capacitance | | – | 17 | – | pF |
| C _{oss(eff.)} | Effective Output Capacitance | V _{DS} = 0 V to 480 V, V _{GS} = 0 V | – | 258 | – | pF |
| Q _{g(tot)} | Total Gate Charge at 10 V | V _{DS} = 380 V, I _D = 14.5 A, V _{GS} = 10 V (Note 4) | – | 75 | 95 | nC |
| Q _{gs} | Gate to Source Gate Charge | | – | 10 | – | nC |
| Q _{gd} | Gate to Drain “Miller” Charge | | – | 33 | – | nC |
| ESR | Equivalent Series Resistance | f = 1 MHz | – | 3.5 | – | Ω |

SWITCHING CHARACTERISTICS

| | | | | | | |
|---------------------|---------------------|---|---|-----|-----|----|
| t _{d(on)} | Turn-On Delay Time | V _{DD} = 380 V, I _D = 14.5 A, V _{GS} = 10 V, R _g = 4.7 Ω (Note 4) | – | 23 | 56 | ns |
| t _r | Turn-On Rise Time | | – | 20 | 50 | ns |
| t _{d(off)} | Turn-Off Delay Time | | – | 106 | 222 | ns |
| t _f | Turn-Off Fall Time | | – | 23 | 56 | ns |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | |
|-----------------|--|---|---|-----|-----|----|
| I _S | Maximum Continuous Source to Drain Diode Forward Current | – | – | 29 | A | |
| I _{SM} | Maximum Pulsed Drain to Source Diode Forward Current | – | – | 87 | A | |
| V _{SD} | Drain to Source Diode Forward Voltage | V _{GS} = 0 V, I _{SD} = 14.5 A | – | – | 1.2 | V |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0 V, I _{SD} = 14.5 A, di _F /dt = 100 A/μs | – | 376 | – | ns |
| Q _{rr} | Reverse Recovery Charge | | – | 6.5 | – | μC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature.

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TYPICAL CHARACTERISTICS

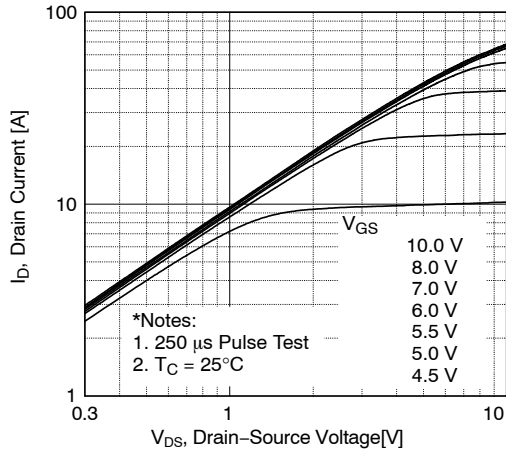


Figure 1. On-Region Characteristics

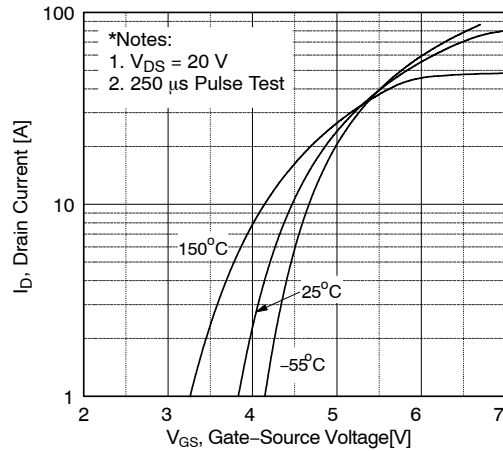


Figure 2. Transfer Characteristics

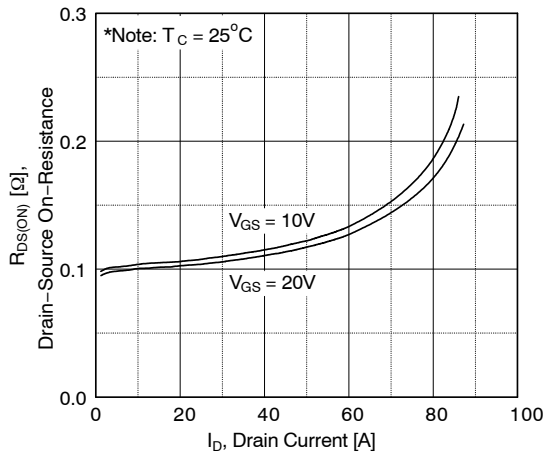


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

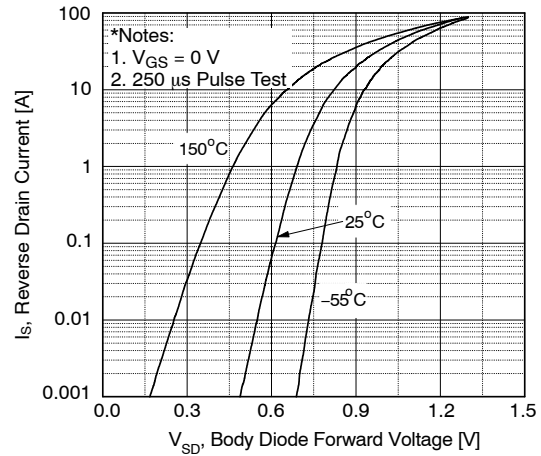


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

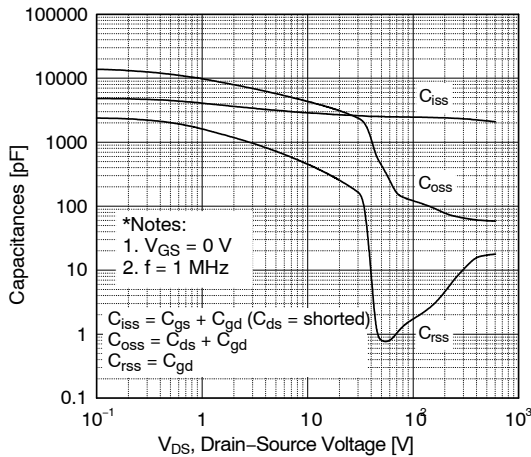


Figure 5. Capacitance Characteristics

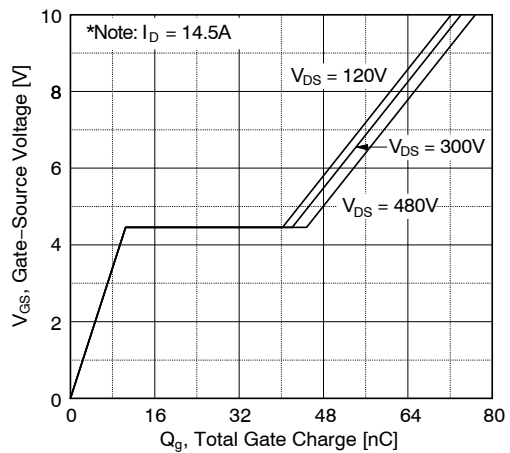


Figure 6. Gate Charge Characteristics

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TYPICAL CHARACTERISTICS

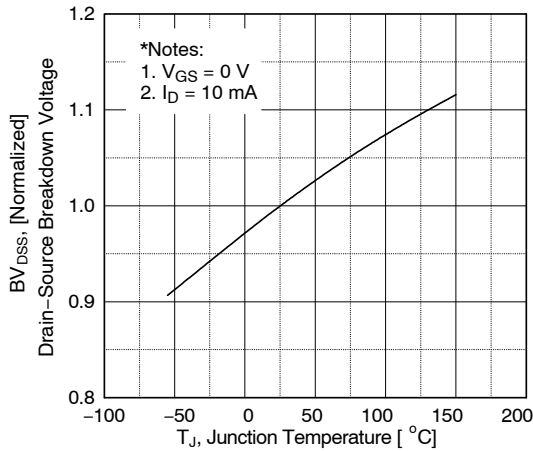


Figure 7. Breakdown Voltage Variation vs. Temperature

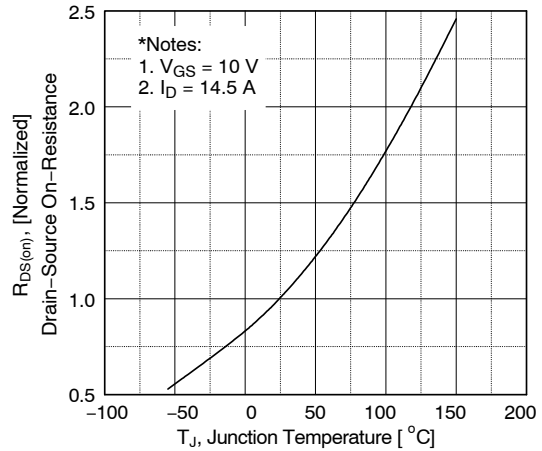


Figure 8. On-Resistance Variation vs. Temperature

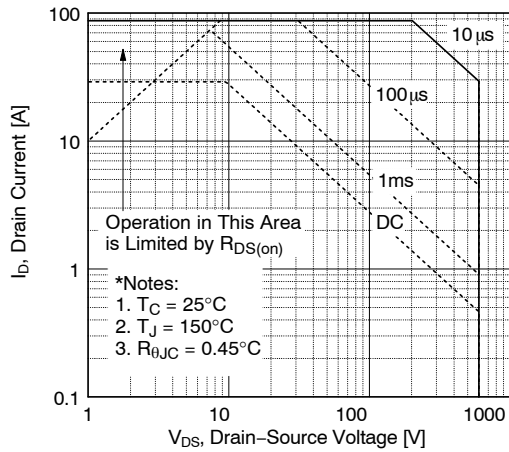


Figure 9. Maximum Safe Operating Area

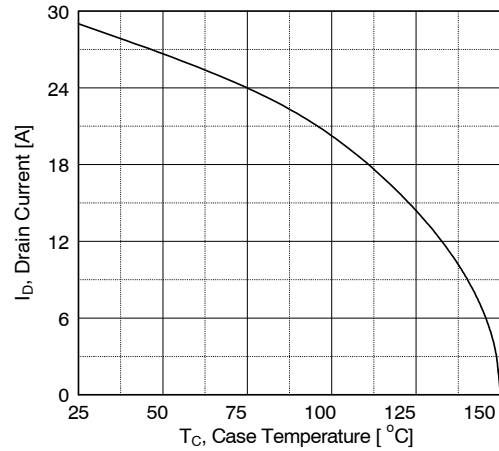


Figure 10. Maximum Drain Current vs. Case Temperature

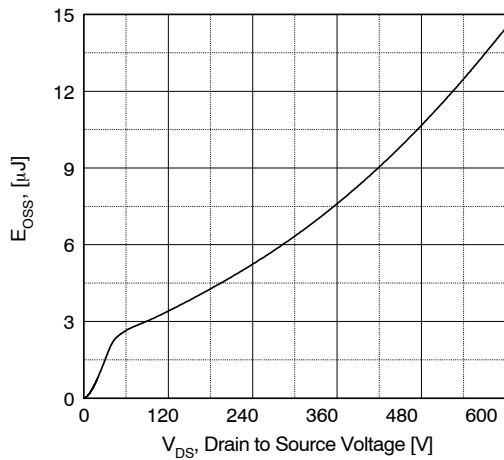


Figure 11. Eoss vs. Drain to Source Voltage

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TYPICAL CHARACTERISTICS

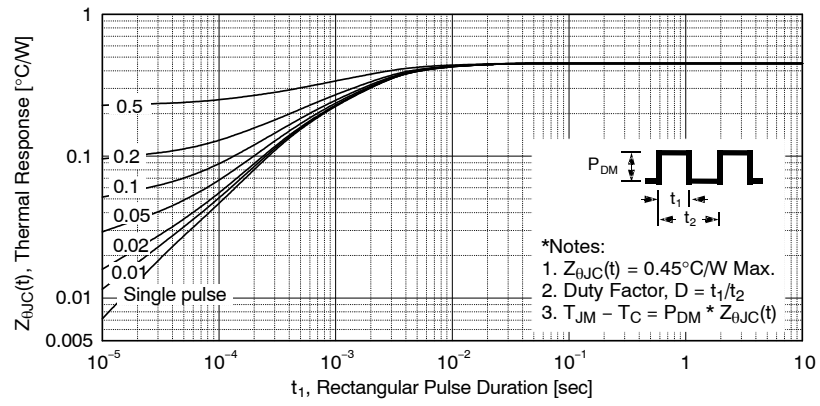


Figure 12. Transient Thermal Response Curve

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Figure 13. Gate Charge Test Circuit & Waveform

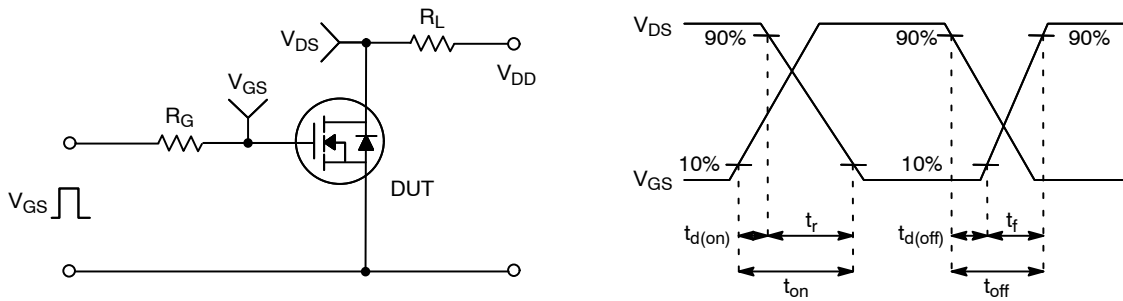


Figure 14. Resistive Switching Test Circuit & Waveforms



Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

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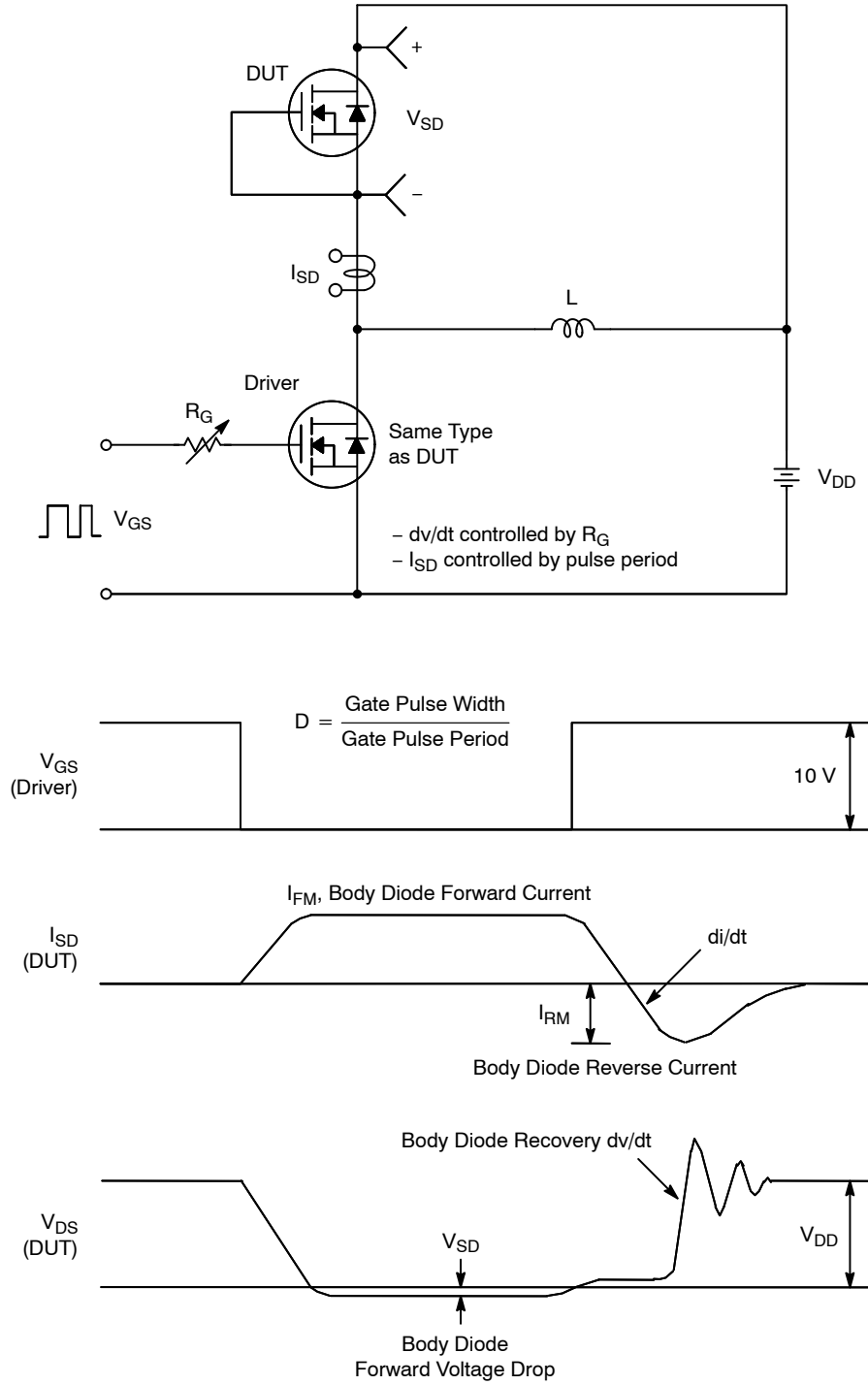


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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TO-247-3LD SHORT LEAD
CASE 340CK
ISSUE A

DATE 31 JAN 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

| DIM | MILLIMETERS | | |
|-----|-------------|-------|-------|
| | MIN | NOM | MAX |
| A | 4.58 | 4.70 | 4.82 |
| A1 | 2.20 | 2.40 | 2.60 |
| A2 | 1.40 | 1.50 | 1.60 |
| b | 1.17 | 1.26 | 1.35 |
| b2 | 1.53 | 1.65 | 1.77 |
| b4 | 2.42 | 2.54 | 2.66 |
| c | 0.51 | 0.61 | 0.71 |
| D | 20.32 | 20.57 | 20.82 |
| D1 | 13.08 | ~ | ~ |
| D2 | 0.51 | 0.93 | 1.35 |
| E | 15.37 | 15.62 | 15.87 |
| E1 | 12.81 | ~ | ~ |
| E2 | 4.96 | 5.08 | 5.20 |
| e | ~ | 5.56 | ~ |
| L | 15.75 | 16.00 | 16.25 |
| L1 | 3.69 | 3.81 | 3.93 |
| ∅P | 3.51 | 3.58 | 3.65 |
| ∅P1 | 6.60 | 6.80 | 7.00 |
| Q | 5.34 | 5.46 | 5.58 |
| S | 5.34 | 5.46 | 5.58 |

| | | |
|-------------------------|-----------------------|--|
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